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RFMD(R) Announces Major Gallium Nitride (GaN) Milestones

RFMD Qualifies and Releases First GaN Device

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Shipments of RF3931 Unmatched Power Transistors Commence to Multiple High Power Amplifier (HPA) Manufacturers

GREENSBORO, N.C., Nov. 11, 2009 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance semiconductor components, today announced that RFMD(R) has qualified and released the RF3931, a 48-volt, 30-watt gallium nitride (GaN) unmatched transistor optimized for high power commercial and defense applications. The RF3931 is RFMD's first GaN product to achieve full product qualification, a process through which RF products are released by RFMD for mass production. Shipments of the RF3931 have commenced to multiple high power amplifier (HPA) manufacturers, and RFMD anticipates GaN shipments will increase significantly as new GaN products are introduced.

Bob Bruggeworth, president and CEO of RFMD, said, "We fully expect RFMD's GaN process technology will play a central role in our corporate mission to extend and leverage our leadership in RF components and compound semiconductor technologies into multiple industries. The unique physical properties of RFMD's GaN technology deliver performance that is unattainable by current competing technologies. Also, RFMD's GaN technology is manufactured in the same high-volume manufacturing facility as our industry-leading GaAs products, providing RFMD a measurable competitive advantage. Accordingly, we believe our GaN technology will become a disruptive technology across a broad range of commercial and defense markets."

Jeff Shealy, VP and general manager of RFMD's Defense and Power business unit, said, "We are very pleased to announce the full product qualification and shipments of RFMD's first GaN product. These achievements are major milestones for RFMD as we drive adoption of our GaN technology, increase our presence in the high-power RF market and satisfy our customers' increasing emphasis on 'green' technologies. RFMD's state-of-the-art GaN process technology delivers superior RF power per square millimeter and superior RF conversion efficiency, as compared to current semiconductor technologies."

The 30-watt RF3931 is part of a family of five RFMD GaN unmatched power transistors to be released for mass production over the next two quarters. Ranging from 10 watts to 120 watts, these wide bandwidth, unmatched power transistors enable the development of high-efficiency HPAs for a broad range of applications, including cellular and WiMAX infrastructure, CATV, military communications, public mobile radio, radar and radar jammers. In wireless and wireline applications, RFMD's unmatched power transistors enable "green" architectures that reduce energy costs and improve network efficiency for network operators.

About the RF3931

RFMD's RF3931 unmatched power transistor achieves high efficiency and flat gain over a broad frequency range in a single amplifier design. The RF3931 is packaged in a hermetic, flanged ceramic package providing excellent thermal stability through the use of advanced heat sink and power dissipation technologies.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering,

design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the recent worldwide economic turmoil and its effect on our business and the business of our suppliers and customers, variability in quarterly operating results, the impact of global macroeconomic and credit conditions on our business, the rate of growth and development of wireless markets, risks associated with the reduction or elimination of our investments in our wireless systems business, risks that restructuring charges may be greater and that the cost savings and other benefits from our restructurings may be lower than originally anticipated, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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